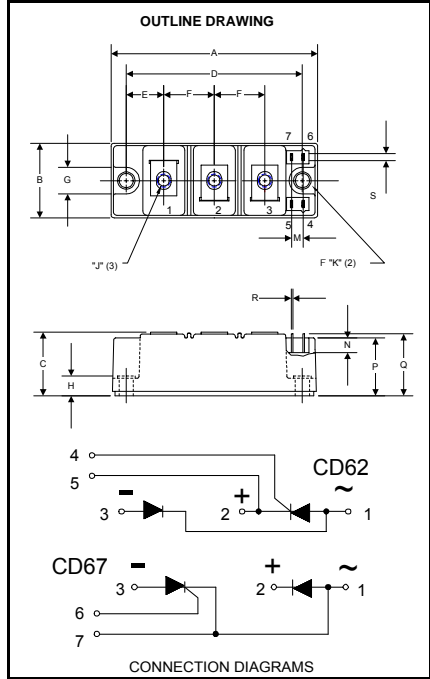


POW-R-BLOK™
Dual SCR/Diode Isolated Module
150 Amperes / Up to 1600 Volts



CD62__15A, CD67__15A
Dual SCR/Diode Isolated
POW-R-BLOK™ Module
150 Amperes / Up to 1600 Volts

Description:

Powerex SCR/Diode Modules are designed for use in applications requiring phase control and isolated packaging. The modules are isolated for easy mounting with other components on a common heatsink. *POW-R-BLOK™* has been tested and recognized by the Underwriters Laboratories.

Features:

- Electrically Isolated Heatsinking
- DBC Alumina (Al₂O₃) Insulator
- Glass Passivated Chips
- Metal Baseplate
- Low Thermal Impedance for Improved Current Capability
- Quick Connect Gate Terminal with Provision for Keyed Mating Plug
- UL Recognized (E78240)

CD62__15A, CD67__15A

Outline Dimensions

| Dimension | Inches | Millimeters |
|-----------|--------|-------------|
| A | 3.70 | 94 |
| B | 1.38 | 35 |
| C | 1.18 | 30 |
| D | 3.15 | 80 |
| E | 0.67 | 17 |
| F | 0.91 | 23 |
| G | 0.57 | 14.5 |
| H | 0.35 | 9 |
| J | M6 | M6 |
| K | 0.26 | 6.5 |
| M | .020 | 5 |
| N | 0.28 | 7 |
| P | 1.10 | 28 |
| Q | 1.14 | 29 |
| R | 0.03 | 0.8 |
| S | 0.11 | 2.8 |

Note: Dimensions are for reference only.

Ordering Information:

Select the complete nine digit module part number from the table below. Example: CD621615A is a 1600Volt, 150 Ampere SCR/Diode Isolated *POW-R-BLOK™* Module

| Type | Voltage Volts (x100) | Current Amperes (x 10) |
|------|----------------------|------------------------|
| CD62 | 08 | 15 |
| CD67 | 12 | |
| | 14 | |
| | 16 | |

Benefits:

- No Additional Insulation Components Required
- Easy Installation
- No Clamping Components Required
- Reduce Engineering Time

Applications:

- Bridge Circuits
- AC & DC Motor Drives
- Battery Supplies
- Power Supplies
- Large IGBT Circuit Front Ends
- Lighting Control
- Heat & Temperature Control
- Welders

Absolute Maximum Ratings

| Characteristics | Conditions | Symbol | Units | |
|---|--|-----------------------|-----------------|------------------------|
| Repetitive Peak Forward and Reverse Blocking Voltage | | V_{DRM} & V_{RRM} | up to 1600 | V |
| Non-Repetitive Peak Reverse Blocking Voltage ($t < 5$ msec) | | V_{RSM} | $V_{RRM} + 100$ | V |
| RMS Forward Current | 180° Conduction, $T_C=85^\circ\text{C}$ | $I_{T(RMS)}$ | 250 | A |
| | 180° Conduction, $T_C=85^\circ\text{C}$ (AC Switch) | $I_{T(RMS)}$ | 355 | A |
| Average Forward Current | 180° Conduction, $T_C=85^\circ\text{C}$ | $I_{T(AV)}$ | 160 | A |
| | 180° Conduction, $T_C=90^\circ\text{C}$ | $I_{T(AV)}$ | 150 | A |
| Peak One Cycle Surge Current, Non-Repetitive | 60 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 4300 | A |
| | 60 Hz, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 5100 | A |
| | 50 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 4100 | A |
| | 50 Hz, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 4870 | A |
| Peak Three Cycle Surge Current, Non-Repetitive | 60 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 3250 | A |
| | 50 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 3150 | A |
| Peak Ten Cycle Surge Current, Non-Repetitive | 60 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 2650 | A |
| | 50 Hz, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I_{TSM} | 2550 | A |
| I^2t for Fusing for One Cycle | 8.3 ms, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I^2t | 76,700 | A^2sec |
| | 8.3 ms, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I^2t | 108,000 | A^2sec |
| | 10 ms, 100% V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I^2t | 84,000 | A^2sec |
| | 10 ms, No V_{RRM} reapplied, $T_j=125^\circ\text{C}$ | I^2t | 119,000 | A^2sec |
| Maximum Rate-of-Rise of On-State Current, Non Repetitive | $T_j=125^\circ\text{C}$, $V_D=1.0 V_{DRM}$ (Rated), $I_{TM}=400\text{A}$, $I_G=0.5\text{A}$, $T_r < 0.25\mu\text{s}$, $t_p > 6\mu\text{s}$ | di/dt | 300 | $\text{A}/\mu\text{s}$ |
| Peak Gate Power Dissipation | $T_p < 5$ ms, $T_j = 125^\circ\text{C}$ | P_{GM} | 12 | W |
| Average Gate Power Dissipation | $F = 50$ Hz, $T_j = 125^\circ\text{C}$ | $P_{G(AV)}$ | 3 | W |
| Peak Forward Gate Current | $T_p < 5$ ms, $T_j = 125^\circ\text{C}$ | I_{GFM} | 3 | A |
| Peak Reverse Gate Voltage | $T_p < 5$ ms, $T_j = 125^\circ\text{C}$ | V_{GRM} | 10 | V |
| Operating Temperature | | T_j | -40 to +125 | $^\circ\text{C}$ |
| Storage Temperature | | T_{stg} | -40 to +150 | $^\circ\text{C}$ |
| Max. Mounting Torque, M6 Mounting Screw on Terminals | | | 35 - 50 | in.-Lb. |
| | | | 4 - 6 | Nm |
| Max. Mounting Torque, Module to Heatsink | | | 35 - 50 | in.-Lb. |
| | | | 4 - 6 | Nm |
| Module Weight, Typical | | | 200 | G |
| | | | 7.1 | Oz. |
| V Isolation @ 25C | | V_{rms} | 3500 | V |

Electrical Characteristics, T_J=25°C unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Max. | Units |
|--|-----------------------------------|---|--------------------------|---|-------------------------|
| Repetitive Peak Forward Leakage Current | I _{DRM} | Up to 1600V, T _J =125°C | | 50 | mA |
| Repetitive Peak Reverse Leakage Current | I _{RRM} | Up to 1600V, T _J =125°C | | 50 | mA |
| Peak On-State Voltage | V _{TM} / V _{FM} | I _{TM} / I _{FM} = 500A | | 1.54 | V |
| Threshold Voltage, Low-level | V _{(TO)1} | T _J = 125°C, I = 16.7% x I _{T(AV)} to I _{T(AV)} | | 0.80 | V |
| Slope Resistance, Low-level | r _{T1} | | | 1.67 | mΩ |
| Threshold Voltage, High-level | V _{(TO)2} | T _J = 125°C, I = I _{T(AV)} to I _{TSM} | | 0.98 | V |
| Slope Resistance, High-level | r _{T2} | | | 1.38 | mΩ |
| V _{TM} Coefficients, Full Range | | T _J = 125°C, I = 15% x I _{T(AV)} to I _{TSM} V _{TM} = A + B Ln I + C I + D Sqrt I | A = B = C = D = | 0.5926 -1.10E-03 1.03E-03 0.0241 | |
| Minimum dV/dt | dV/dt | Exponential to 2/3 V _{DRM} T _J =125°C, Gate Open | 1000 | | V/μs |
| Turn-On Time (Typical) | t _{on} | I _{TM} = 300A, V _D = 2/3 V _{DRM} dI _G /dt = 1A/μs | 3 | (Typical) | μs |
| Turn-Off Time (Typical) | t _{off} | T _J = 125°C, I _T = 300A, R _{gk} = 100Ω V _r = 50V, -dI/dt = 15 A/μs Re-Applied dV/dt = 20V/μs, Linear to 2/3 V _{DRM} | 50 - 200 | (Typical) | μs |
| Gate Trigger Current | I _{GT} | T _J = -40°C, V _D = 6V, R _a = 1Ω, Resistive Load T _J = 25°C, V _D = 6V, R _a = 1Ω, Resistive Load T _J = 125°C, V _D = 6V, R _a = 1Ω, Resistive Load | | 270 150 80 | mA mA mA |
| Gate Trigger Voltage | V _{GT} | T _J = -40°C, V _D = 6V, R _a = 1Ω, Resistive Load T _J = 25°C, V _D = 6V, R _a = 1Ω, Resistive Load T _J = 125°C, V _D = 6V, R _a = 1Ω, Resistive Load | | 4.0 2.5 1.7 | Volts Volts Volts |
| Non-Triggering Gate Voltage | V _{GDM} | T _J = 125°C, V _D = V _{DRM} | | 0.30 | Volts |
| Non-Triggering Gate Current | I _{GDM} | T _J = 125°C, V _D = V _{DRM} | | 10 | mA |

Thermal Characteristics

| Characteristics | Symbol | | Max. | Units |
|--|-------------------|--|--|---|
| Thermal Resistance, Junction to Case DC Operation | R _{ΘJ-C} | Per Module, both conducting Per Junction, both conducting | 0.08 0.16 | °C/W °C/W |
| Thermal Impedance Coefficients (Per Junction) | Z _{ΘJ-C} | Z _{ΘJ-C} = K ₁ (1-exp(-t/τ ₁)) + K ₂ (1-exp(-t/τ ₂)) + K ₃ (1-exp(-t/τ ₃)) + K ₄ (1-exp(-t/τ ₄)) | K ₁ = 5.45334E-3 K ₂ = 3.8509E+1 K ₃ = -3.5154E+1 K ₄ = -3.20 | τ ₁ = 4.511E-5 τ ₂ = 1.3558E-1 τ ₃ = 1.3311E-1 τ ₄ = 1.5936E-1 |
| Thermal Resistance, Case to Sink Lubricated | R _{ΘC-S} | Per Module | 0.05 | °C/W |